

ABSTRACT OF THE DISCLOSURE

Semiconductor device 3 comprises semiconductor chip 11, Au ball bumps 21 formed on pad electrodes 12 with a stud bump method, and thermoplastic adhesive layer 22 provided on the surface of semiconductor chip 11 on which pad electrodes 12 are formed, in which the tops of Au ball bumps 21 project from the surface of adhesive layer 22. Reliable bonding can be realized by forming the bumps for electrical connection and the adhesive resin having an adhesion function on the semiconductor chip. In addition, the present invention provides a method of bonding a copper foil to a semiconductor wafer to form a wiring pattern, a multi chip module in which electrical connection is established by bumps bonded to each other through an adhesive layer, and the like.